

High-speed diode

DESCRIPTION

The LBAS516T1 is a high-speed switching diode fabricated in planar technology, and encapsulated in the SOD523 (SC79) SMD plastic package.

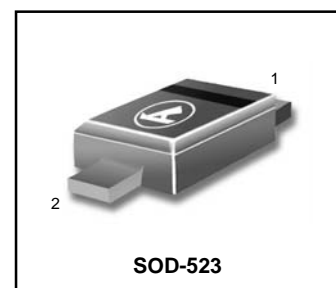
FEATURES

- Ultra small plastic SMD package
 - High switching speed: max. 4 ns
 - Continuous reverse voltage: max. 75 V
 - Repetitive peak reverse voltage: max. 85 V
 - Repetitive peak forward current: max. 500 mA.
- We declare that the material of product compliance with RoHS requirements.

APPLICATIONS

- High-speed switching in e.g. surface mounted circuits.

LBAS516T1G



ORDERING INFORMATION

Device	Marking	Shipping
LBAS516T1G	6	3000 Tape & Reel
LBAS516T3G	6	10000 Tape & Reel

ELECTRICAL CHARACTERISTICS $T_j=25^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.2 $I_F = 1 \text{ mA}$	715	mV
		$I_F = 10 \text{ mA}$	855	mV
		$I_F = 50 \text{ mA}$	1	V
		$I_F = 150 \text{ mA}$	1.25	V
I_R	reverse current	see Fig.4 $V_R = 25 \text{ V}$	30	nA
		$V_R = 75 \text{ V}$	1	μA
		$V_R = 25 \text{ V}; T_j = 150^{\circ}\text{C}$	30	μA
		$V_R = 75 \text{ V}; T_j = 150^{\circ}\text{C};$	50	μA
C_d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0; \text{ see Fig.5}$	1	pF
t_{rr}	reverse recovery time	when switched from $I_F = 10 \text{ mA}$ to $I_R = 10 \text{ mA};$ $R_L = 100 \Omega; \text{ measured at } I_R = 1 \text{ mA}; \text{ see Fig.6}$	4	ns
V_{fr}	forward recovery voltage	when switched from $I_F = 10 \text{ mA}; t_r = 20 \text{ ns}; \text{ see Fig.7}$	1.75	V

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R_{thj-s}	thermal resistance from junction to soldering point	note 1	120	K/W

Note 1. Soldering point of the cathode tab.

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LIMITING VALUES In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT	
V_{RRM}	repetitive peak reverse voltage		–	85	V	
V_R	continuous reverse voltage		–	75	V	
I_F	continuous forward current	$T_s=90^\circ\text{C}$; note 1; see Fig.1	–	250	mA	
I_{FRM}	repetitive peak forward current		–	500	mA	
I_{FSM}	non-repetitive peak forward current	square wave; $T_j=25^\circ\text{C}$ prior to surge; see Fig.3				
			$t=1\mu\text{s}$	–	4	A
			$t=1\text{ ms}$	–	1	A
			$t=1\text{ s}$	–	0.5	A
P_{tot}	total power dissipation	$T_s=90^\circ\text{C}$; note 1	–	500	mW	
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$	
T_j	junction temperature		–	150	$^\circ\text{C}$	

Note

1. T_s is the temperature at the soldering point of the cathode tab.

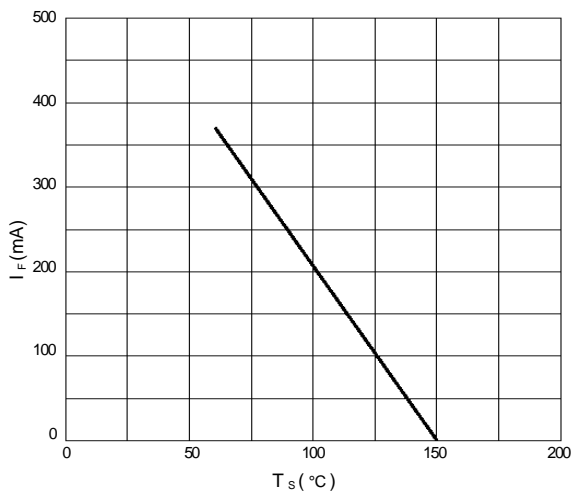


Fig.1 Maximum permissible continuous forward current as a function of soldering point temperature.

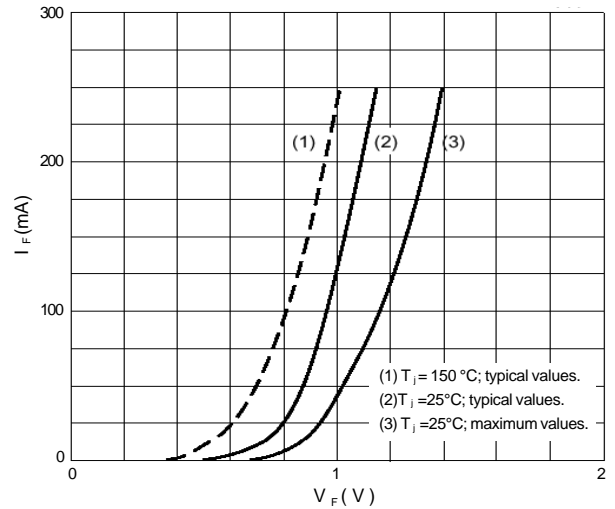


Fig.2 Forward current as a function of forward voltage.

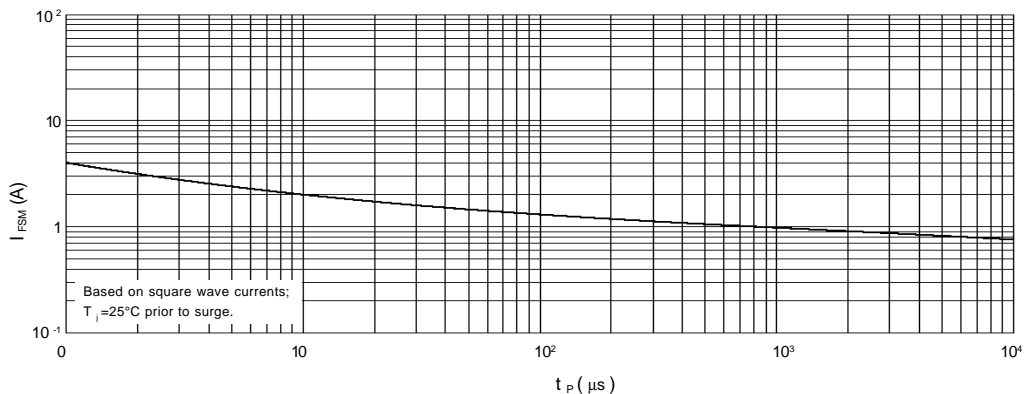


Fig.3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

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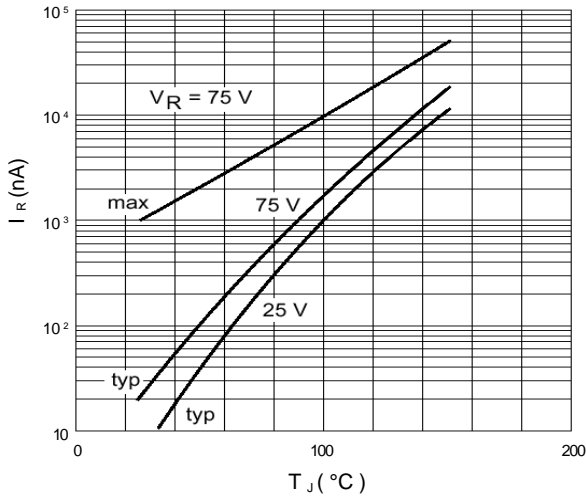


Fig.4 Reverse current as a function of junction temperature.

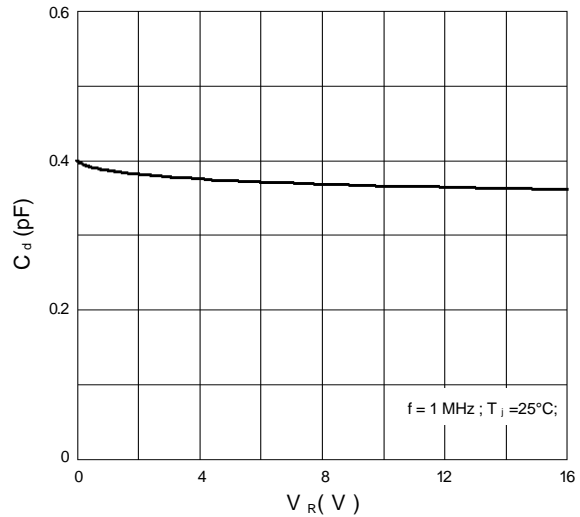
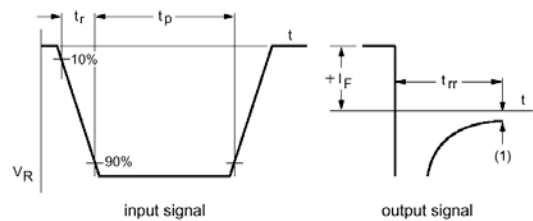
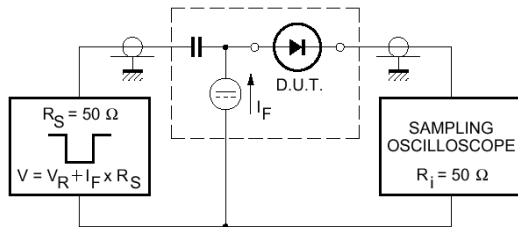
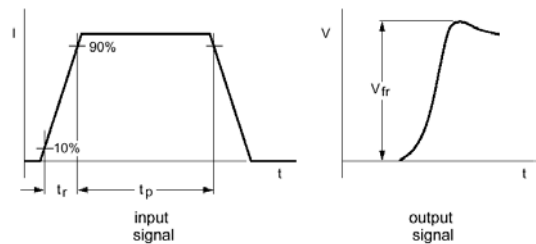
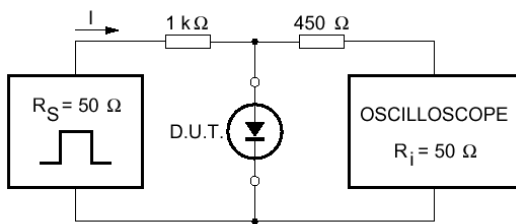


Fig.5 Diode capacitance as a function of reverse voltage; typical values.



(1) $I_R = 1 \text{ mA}$.
 Input signal: reverse pulse rise time $t_r = 0.6 \text{ ns}$; reverse voltage pulse duration $t_p = 100 \text{ ns}$; duty factor $\delta = 0.05$;
 Oscilloscope: rise time $t_r = 0.35 \text{ ns}$.

Fig.6 Reverse recovery voltage test circuit and waveforms.

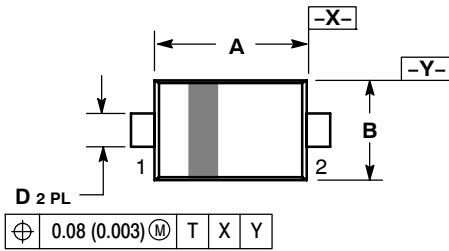


Input signal: forward pulse rise time $t_r = 20 \text{ ns}$; forward current pulse duration $t_p \geq 100 \text{ ns}$; duty factor $\delta \leq 0.005$.

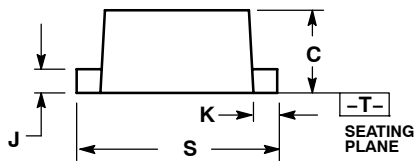
Fig.7 Forward recovery voltage test circuit and waveforms.

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SOD-523



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.10	1.20	1.30	0.043	0.047	0.051
B	0.70	0.80	0.90	0.028	0.032	0.035
C	0.50	0.60	0.70	0.020	0.024	0.028
D	0.25	0.30	0.35	0.010	0.012	0.014
J	0.07	0.14	0.20	0.0028	0.0055	0.0079
K	0.15	0.20	0.25	0.006	0.008	0.010
S	1.50	1.60	1.70	0.059	0.063	0.067



SOLDERING FOOTPRINT*

